

# Michael Seibt

## List of Publications by Year in descending order

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175  
papers

4,431  
citations

126858

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180  
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180  
docs citations

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times ranked

4163  
citing authors

#	ARTICLE	IF	CITATIONS
1	Orbital-order phase transition in $\text{PrMnO}_3$ probed by photovoltaics. <i>Physical Review B</i> , 2021, 103, .		
2	Phase Transitions in a Perovskite Thin Film Studied by Environmental In Situ Heating Nano-Beam Electron Diffraction. <i>Small Methods</i> , 2021, 5, e2100464.	4.6	2
3	Recombination and Charge Collection at Nickel Silicide Precipitates in Silicon Studied by Electron Beam-Induced Current. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2100142.	0.7	1
4	Site-specific plan-view TEM lamella preparation of pristine surfaces with a large field of view. <i>Ultramicroscopy</i> , 2021, 228, 113320.	0.8	1
5	Phase Transitions in a Perovskite Thin Film Studied by Environmental In Situ Heating Nano-Beam Electron Diffraction (Small Methods 9/2021). <i>Small Methods</i> , 2021, 5, 2170042.	4.6	0
6	Environmental transmission electron microscopy study of hydrogen charging effect on a Cu-Zr metallic glass. <i>Materials Research Letters</i> , 2020, 8, 439-445.	4.1	3
7	Room-Temperature Hot-Polaron Photovoltaics in the Charge-Ordered State of a Layered Perovskite Oxide Heterojunction. <i>Physical Review Applied</i> , 2020, 14, .	1.5	6
8	Extended core structure and luminescence of a-screw dislocations in GaN. <i>Journal of Physics: Conference Series</i> , 2019, 1190, 012006.	0.3	3
9	High-resolution Scanning Transmission EBIC Analysis of Misfit Dislocations at Perovskite pn-Heterojunctions. <i>Journal of Physics: Conference Series</i> , 2019, 1190, 012009.	0.3	4
10	Preparation Techniques for Cross-Section Transmission Electron Microscopy Lamellas Suitable for Investigating In Situ Silicon-Aluminum Alloying at Grain Boundaries in Multicrystalline Silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900308.	0.8	2
11	A posteriori synchronization of scanning transmission electron microscopy signals with kilopixel per second acquisition rates. <i>Ultramicroscopy</i> , 2019, 200, 62-66.	0.8	1
12	Correlation of structure and intrinsic luminescence of freshly introduced dislocations in GaN revealed by SEM and TEM. <i>AIP Conference Proceedings</i> , 2019, , .	0.3	2
13	Intrinsic luminescence and core structure of freshly introduced a-screw dislocations in n-GaN. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	26
14	Formation of porous silicon oxide from substrate-bound silicon rich silicon oxide layers by continuous-wave laser irradiation. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	1
15	Concerning vacancy defects generated by moving dislocations in Si. <i>Materials Today: Proceedings</i> , 2018, 5, 14757-14764.	0.9	8
16	Low energy scanning transmission electron beam induced current for nanoscale characterization of pn junctions. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1600358.	1.2	3
17	Microscopic electronic and structural analysis of femtosecond laser sulfur hyperdoped silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700264.	0.8	6
18	Microstructural analysis of the modifications in substrate-bound silicon-rich silicon oxide induced by continuous wave laser irradiation. <i>Journal of Alloys and Compounds</i> , 2017, 707, 227-232.	2.8	3

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19	Contribution of Jahn-Teller and charge transfer excitations to the photovoltaic effect of manganese/titanite heterojunctions. <i>New Journal of Physics</i> , 2017, 19, 063046.	1.2	11
20	Study of the structure and composition of the strained epitaxial layer in the InAlAs/GaAs(100) heterostructure by transmission electron microscopy. <i>Semiconductors</i> , 2016, 50, 1753-1758.	0.2	0
21	Recombination-related properties of a-screw dislocations in GaN: A combined CL, EBIC, TEM study. <i>AIP Conference Proceedings</i> , 2016, , .	0.3	8
22	Quantitative assessment of molecular dynamics-grown amorphous silicon and germanium films on silicon (111). <i>Surface Science</i> , 2016, 651, 100-104.	0.8	4
23	Graphene quantum dots with visible light absorption of the carbon core: insights from single-particle spectroscopy and first principles based theory. <i>2D Materials</i> , 2016, 3, 041008.	2.0	4
24	The influence of the atomic structure of basal planes on interplanar distance in pyrolytic carbon materials. <i>Technical Physics Letters</i> , 2016, 42, 1137-1140.	0.2	3
25	Implantation of plasmonic nanoparticles in SiO <sub>2</sub> by pulsed laser irradiation of gold films on SiO <sub>2</sub> -coated fused silica and subsequent thermal annealing. <i>Applied Surface Science</i> , 2016, 374, 138-142.	3.1	6
26	Spin-Transfer Torque Switching at Ultra Low Current Densities. <i>Materials Transactions</i> , 2015, 56, 1323-1326.	0.4	15
27	Generation of silicon nanocrystals by damage free continuous wave laser annealing of substrate-bound SiO <sub>x</sub> films. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	9
28	On the nature of defects produced by motion of dislocations in silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 1695-1703.	0.8	16
29	Turbostratic pyrocarbon structure study by means of exit wave reconstruction from high-resolution transmission electron microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 1179-1182.	0.8	2
30	Structural studies of Al thin layer on misoriented GaAs(100) substrate by transmission electron microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 1148-1151.	0.8	1
31	Current-voltage characteristics of manganese-titanite perovskite junctions. <i>Beilstein Journal of Nanotechnology</i> , 2015, 6, 1467-1484.	1.5	16
32	Electron microscopy study of turbostratic pyrolytic carbon atomic structure using the exit wave reconstruction technique. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2015, 79, 1353-1359.	0.1	1
33	Phonon localization in ultrathin layered structures. <i>Applied Physics A: Materials Science and Processing</i> , 2015, 119, 11-18.	1.1	8
34	Electron microscopy of an aluminum layer grown on the vicinal surface of a gallium arsenide substrate. <i>Semiconductors</i> , 2015, 49, 337-344.	0.2	4
35	Temperature and bias-voltage dependence of atomic-layer-deposited HfO <sub>2</sub> -based magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	8
36	Epitaxial growth of gold on Si(001). <i>Surface Science</i> , 2014, 624, 15-20.	0.8	8

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37	Photoluminescence of Carbon Nanodots: Dipole Emission Centers and Electron-Phonon Coupling. Nano Letters, 2014, 14, 5656-5661.	4.5	187
38	Electronic and structural properties of femtosecond laser sulfur hyperdoped silicon pn-junctions. Applied Physics Letters, 2013, 103, .	1.5	15
39	Transmission electron microscopy analysis of extended defects in multicrystalline silicon using in-situ EBIC/FIB sample preparation. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 32-35.	0.8	1
40	PARAMETER SPACE FOR THERMAL SPIN-TRANSFER TORQUE. Spin, 2013, 03, 1350002.	0.6	29
41	Interaction of Iron with Extended Defects in Multicrystalline Silicon Studied by Local Gettering. Energy Procedia, 2013, 38, 582-588.	1.8	2
42	Mesoscopic properties of interfacial ordering in amorphous germanium on Si(111) determined by quantitative digital image series matching. Ultramicroscopy, 2013, 126, 1-9.	0.8	2
43	Characterization of Electrical Contacts on Silicon (100) after Ablation and Sulfur Doping by Femtosecond Laser Pulses. Solid State Phenomena, 2013, 205-206, 358-363.	0.3	1
44	Platinum and gold diffusion monitor vacancy profiles induced into silicon wafers by aluminum alloying. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 771-776.	0.8	3
45	Tailoring the Absorption Properties of Black Silicon. Energy Procedia, 2012, 27, 480-484.	1.8	11
46	Electronic and chemical properties of the c-Si/Al <sub>2</sub> O <sub>3</sub> interface. Journal of Applied Physics, 2011, 109, .	1.1	210
47	Structure and Elemental Distribution of (Ga,Mn)N Nanowires. Nano Letters, 2011, 11, 398-401.	4.5	13
48	Transmission Electron Microscopy Investigations of Metal-Impurity-Related Defects in Crystalline Silicon. Solid State Phenomena, 2011, 178-179, 275-284.	0.3	2
49	Seebeck effect in magnetic tunnel junctions. Nature Materials, 2011, 10, 742-746.	13.3	260
50	Tunnel magnetoresistance in alumina, magnesia and composite tunnel barrier magnetic tunnel junctions. Journal of Magnetism and Magnetic Materials, 2011, 323, 1525-1528.	1.0	4
51	Tailored Synthetic Polyamines for Controlled Biomimetic Silica Formation. Journal of the American Chemical Society, 2010, 132, 1023-1031.	6.6	88
52	Effect of Au contamination on the electrical characteristics of a model small-angle grain boundary in n-type direct silicon bonded wafer. Journal of Applied Physics, 2010, 108, 053719.	1.1	8
53	Impact of surface topography and laser pulse duration for laser ablation of solar cell front side passivating SiNx layers. Journal of Applied Physics, 2010, 108, 114514.	1.1	42
54	Localization and preparation of recombination-active extended defects for transmission electron microscopy analysis. Review of Scientific Instruments, 2010, 81, 063705.	0.6	11

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55	Elastic and inelastic conductance in Co-Fe-B/MgO/Co-Fe-B magnetic tunnel junctions. <i>Physical Review B</i> , 2010, 82, .	1.1	18
56	Light-induced point defect reactions of residual iron in crystalline silicon after aluminum gettering. <i>Journal of Applied Physics</i> , 2010, 108, 043519.	1.1	11
57	Epitaxial growth and stress relaxation of vapor-deposited Fe-Pd magnetic shape memory films. <i>New Journal of Physics</i> , 2009, 11, 113054.	1.2	32
58	Self-organized formation of layered carbon-copper nanocomposite films by ion deposition. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2009, 267, 1356-1359.	0.6	4
59	Electronic states at dislocations and metal silicide precipitates in crystalline silicon and their role in solar cell materials. <i>Applied Physics A: Materials Science and Processing</i> , 2009, 96, 235-253.	1.1	90
60	Combined XRD/XRF/XAS/DLTS investigation of chemical character and electrical properties of Cu and Ni precipitates in silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 1868-1873.	0.8	6
61	Structure, chemistry and electrical properties of extended defects in crystalline silicon for photovoltaics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 1847-1855.	0.8	12
62	Localisation and identification of recombination-active extended defects in crystalline silicon by means of focused ion-beam preparation and transmission electron microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 1862-1867.	0.8	3
63	Co-precipitation of copper and nickel in crystalline silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 365-368.	1.7	12
64	Light-beam-induced current measurements on copper-nickel co-contaminated Cz-silicon bicrystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 216-218.	1.7	7
65	Interaction of metal impurities with extended defects in crystalline silicon and its implications for gettering techniques used in photovoltaics. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 264-268.	1.7	22
66	Optimization of nanopores obtained by chemical etching on swift-ion irradiated lithium niobate. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2009, 267, 1035-1038.	0.6	10
67	Synchrotron-based investigation of iron precipitation in multicrystalline silicon. <i>Superlattices and Microstructures</i> , 2009, 45, 168-176.	1.4	12
68	Aluminum gettering of iron in silicon as a problem of the ternary phase diagram. <i>Applied Physics Letters</i> , 2009, 94, 061912.	1.5	20
69	Electric breakdown in ultrathin MgO tunnel barrier junctions for spin-transfer torque switching. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	25
70	Long-range order on the atomic scale induced at CoFeB/MgO interfaces. <i>Journal of Applied Physics</i> , 2009, 105, 073701.	1.1	5
71	Influence of the Dislocation Travel Distance on the DLTS Spectra of Dislocations in Cz-Si. <i>Solid State Phenomena</i> , 2008, 131-133, 175-182.	0.3	14
72	Self-organized growth of In nanocolumns on Si(111) by MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1706-1708.	0.8	21

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73	Influence of the Mn compositional distribution on the magnetic order in diluted GaMnN layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1832-1835.	0.8	1
74	Disturbance of Tunneling Coherence by Oxygen Vacancy in Epitaxial $\text{Fe}/\text{MgO}/\text{Fe}$ Tunnel Junctions. Physical Review Letters, 2008, 100, 246803.	2.9	96
75	Electron microscopy analysis of silicon islands and line structures formed on screen-printed Al-doped p-type surfaces. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	0
76	Direct imaging of the structural change generated by dielectric breakdown in MgO based magnetic tunnel junctions. Applied Physics Letters, 2008, 93, 152508.	1.5	15
77	Charge pattern formation at silicon surfaces for defined biomolecule adsorption. AIP Conference Proceedings, 2008, , .	0.3	0
78	Electron microscopy analysis of crystalline silicon islands formed on screen-printed aluminum-doped p-type silicon surfaces. Journal of Applied Physics, 2008, 104, 043701.	1.1	21
79	Epitaxial growth of MgO and $\text{Fe}/\text{MgO}/\text{Fe}$ magnetic tunnel junctions on (100)-Si by molecular beam epitaxy. Applied Physics Letters, 2008, 93, .	1.5	45
80	Substitutional-to-interstitial ratio of manganese in nanostructured GaN by electron channeling enhanced microanalysis. Journal of Applied Physics, 2008, 103, 073520.	1.1	3
81	P-type doping of GaAs nanowires. Applied Physics Letters, 2008, 92, 163107.	1.5	39
82	Microstructure and twinning in epitaxial NiMnGa films. Physical Review B, 2008, 78, .	1.1	30
83	Structural Investigation of Amorphous/Crystalline Interfaces by Iterative Digital Image Series Matching. , 2008, , 155-156.		0
84	Transmission Electron Microscopy Investigation of Self-Organized InN Nano-columns. , 2008, , 93-94.		0
85	Measurement of the ratio of substitutional to interstitial dopant-incorporation in nanostructures. Microscopy and Microanalysis, 2007, 13, 428-429.	0.2	0
86	Nanostructure of chemically phase separated $\text{La}/\text{Ce}/\text{Mn}/\text{O}$ thin films. Applied Physics Letters, 2007, 91, 132508.	1.5	4
87	Intra-atomic photoluminescence at 1.41 eV of substitutional Mn in GaMnN of high optical quality. Journal of Applied Physics, 2007, 101, 063504.	1.1	23
88	Nanofabrication of spin-transfer torque devices by a polymethylmethacrylate mask one step process: Giant magnetoresistance versus single layer devices. Journal of Applied Physics, 2007, 101, 104302.	1.1	5
89	Impact of $\text{NiSi}_2$ Precipitates Electronic Structure on the Minority Carrier Lifetime in n-and p-Type Silicon. Solid State Phenomena, 2007, 131-133, 155-160.	0.3	5
90	A metallic glass composite: Phase-field simulations and experimental analysis of microstructure evolution. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2007, 452-453, 8-14.	2.6	6

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91	High resolution imaging of extended defects in GaN using wave function reconstruction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 3010-3014.	0.8	11
92	Regular Dislocation Networks in Silicon as a Tool for Nanostructure Devices used in Optics, Biology, and Electronics. <i>Small</i> , 2007, 3, 964-973.	5.2	50
93	Electrical properties of gold in dislocated silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007, 204, 2185-2189.	0.8	4
94	Deposition and properties of high-carbon iron films. <i>Applied Surface Science</i> , 2007, 254, 955-960.	3.1	4
95	Luminescence centres in silica nanowires. <i>Nanotechnology</i> , 2006, 17, 3215-3218.	1.3	41
96	Pattern Recognition in High-Resolution Electron Microscopy of Complex Materials. <i>Microscopy and Microanalysis</i> , 2006, 12, 476-482.	0.2	1
97	Gettering in silicon photovoltaics: current state and future perspectives. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 696-713.	0.8	52
98	Self-organized pattern formation of biomolecules at silicon surfaces: Intended application of a dislocation network. <i>Materials Science and Engineering C</i> , 2006, 26, 902-910.	3.8	21
99	Self-assembled nano-scale multilayer formation using physical vapor deposition methods. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2006, 242, 261-264.	0.6	9
100	Mn incorporation in GaN thin layers grown by molecular-beam epitaxy. <i>Semiconductor Science and Technology</i> , 2006, 21, 1348-1353.	1.0	11
101	Decomposition and metastable phase formation in the bulk metallic glass matrix composite Zr <sub>56</sub> Ti <sub>14</sub> Nb <sub>5</sub> Cu <sub>7</sub> Ni <sub>6</sub> Be <sub>12</sub> . <i>Journal of Applied Physics</i> , 2006, 99, 123519.	1.1	9
102	Dendritic microstructure in the metallic glass matrix composite Zr <sub>56</sub> Ti <sub>14</sub> Nb <sub>5</sub> Cu <sub>7</sub> Ni <sub>6</sub> Be <sub>12</sub> . <i>Scripta Materialia</i> , 2005, 53, 93-97.	2.6	21
103	Early stages of iron precipitation in silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1802-1806.	0.8	7
104	Electrical properties of gold at dislocations in silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1847-1851.	0.8	5
105	Silicon light-emitting diodes based on dislocation-related luminescence. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 901-910.	0.8	60
106	Structural and electrical properties of metal impurities at dislocations in silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 911-920.	0.8	47
107	Electrical Properties of Clustered and Precipitated Iron in Silicon. <i>Solid State Phenomena</i> , 2005, 108-109, 109-114.	0.3	2
108	Co-rich magnetic amorphous films and their application in magnetoelectronics. <i>Physical Review B</i> , 2005, 72, .	1.1	11

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109	Gold nanoclusters on amorphous carbon synthesized by ion-beam deposition. Journal of Applied Physics, 2005, 98, 034304.	1.1	17
110	Nucleation mechanism of the seed of tetrapod ZnO nanostructures. Journal of Applied Physics, 2005, 98, 034307.	1.1	82
111	Interaction of Interstitially Dissolved Cobalt and Oxygen-Related Centres in Silicon. Solid State Phenomena, 2004, 95-96, 553-558.	0.3	3
112	Microstructural and Electrical Properties of NiSi <sub>2</sub> Precipitates at Dislocations in Silicon. Solid State Phenomena, 2004, 95-96, 447-452.	0.3	5
113	Phosphorus Diffusion Gettering of Metallic Impurities in Silicon: Mechanisms beyond Segregation. Solid State Phenomena, 2004, 95-96, 527-538.	0.3	9
114	Atomic structure of the interface between silicon (111) and amorphous germanium. Physical Review B, 2004, 70, .	1.1	14
115	Self-organized nanoscale multilayer growth in hyperthermal ion deposition. Physical Review B, 2004, 70, .	1.1	32
116	The effect of the translational symmetry of crystalline silicon on the structure of amorphous germanium in the interfacial region. Crystallography Reports, 2004, 49, 225-232.	0.1	2
117	High-Resolution Electron Microscopy of Interfaces between Solids with Varying Degree of Atomic Ordering. Journal of Materials Science, 2004, 12, 311-319.	1.2	2
118	Phase separation and magnetic properties of Nd <sub>60</sub> Fe <sub>30</sub> Al <sub>10</sub> thin films. Applied Physics Letters, 2004, 85, 2565-2567.	1.5	4
119	Room-temperature silicon light-emitting diodes based on dislocation luminescence. Applied Physics Letters, 2004, 84, 2106-2108.	1.5	166
120	Influence of a ZnMnTe buffer layer on the growth of ZnTe on (001)GaAs by MOVPE. Journal of Crystal Growth, 2003, 249, 15-22.	0.7	12
121	Ion energy thresholds and stability of cubic boron nitride. Diamond and Related Materials, 2003, 12, 1877-1882.	1.8	12
122	Ion beam synthesis of diamond-like carbon thin films containing copper nanocrystals. Journal of Applied Physics, 2003, 93, 1203-1207.	1.1	29
123	Electrical Activity of Dislocations in Si Decorated by Ni. Solid State Phenomena, 2002, 82-84, 361-366.	0.3	10
124	Microstructure-controlled magnetic properties of the bulk glass-forming alloy Nd <sub>60</sub> Fe <sub>30</sub> Al <sub>10</sub> . Applied Physics Letters, 2002, 80, 1749-1751.	1.5	83
125	Influence of deposition conditions on Ir/IrO <sub>2</sub> oxygen barrier effectiveness. Journal of Applied Physics, 2002, 91, 9591.	1.1	34
126	Oxygen tracer diffusion in IrO <sub>2</sub> barrier films. Journal of Applied Physics, 2002, 91, 1707-1709.	1.1	21



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127	Analysis of high resolution transmission electron microscope images of crystalline-amorphous interfaces. Ultramicroscopy, 2002, 90, 241-258.	0.8	15
128	Structural and optical properties of $\text{FeSi}_2$ layers grown by ion beam mixing. Surface and Coatings Technology, 2002, 158-159, 198-202.	2.2	5
129	Exploiting long-range atomic ordering for the investigation of strain relaxation in lattice-mismatched epitaxy. Applied Surface Science, 2002, 188, 61-68.	3.1	11
130	Ion beam synthesis of amorphous carbon thin films containing metallic nanoclusters. Surface and Coatings Technology, 2002, 158-159, 114-119.	2.2	25
131	Mechanisms and computer modelling of transition element gettering in silicon. Solar Energy Materials and Solar Cells, 2002, 72, 299-313.	3.0	20
132	Growth of $\text{FeSi}_2$ films via noble-gas ion-beam mixing of Fe/Si bilayers. Journal of Applied Physics, 2001, 90, 4474-4484.	1.1	36
133	Order and disorder in epitaxially grown $\text{CuInS}_2$ . Thin Solid Films, 2001, 387, 83-85.	0.8	25
134	Preparation and properties of dc-sputtered $\text{IrO}_2$ and Ir thin films for oxygen barrier applications in advanced memory technology. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1857.	1.6	41
135	Nanocrystallization of amorphous-Ta <sub>40</sub> Si <sub>14</sub> N <sub>46</sub> diffusion barrier thin films. Applied Physics Letters, 2001, 78, 3618-3620.	1.5	11
136	Cubic boron nitride thin film heteroepitaxy. Journal of Applied Physics, 2001, 90, 3248-3254.	1.1	33
137	Investigation of oxygen diffusion barrier properties of reactively sputtered $\text{IrO}_2$ thin films. Integrated Ferroelectrics, 2001, 37, 29-38.	0.3	1
138	Phosphorus Diffusion Gettering of Platinum in Silicon: Formation of Near-Surface Precipitates. Physica Status Solidi (B): Basic Research, 2000, 222, 327-336.	0.7	8
139	Simulation of Al and phosphorus diffusion gettering in Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 175-181.	1.7	34
140	Atomic structure and electronic states of nickel and copper silicides in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 72, 80-86.	1.7	36
141	Structural and electronic properties of epitaxially grown $\text{CuInS}_2$ films. Thin Solid Films, 2000, 361-362, 504-508.	0.8	33
142	Mechanisms of transition-metal gettering in silicon. Journal of Applied Physics, 2000, 88, 3795.	1.1	246
143	Structural and Electrical Properties of Metal Silicide Precipitates in Silicon. Physica Status Solidi A, 1999, 171, 301-310.	1.7	74
144	Formation and Properties of Copper Silicide Precipitates in Silicon. Physica Status Solidi A, 1998, 166, 171-182.	1.7	67

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145	Sensitivity limits of strain mapping procedures using high-resolution electron microscopy. Journal of Microscopy, 1998, 190, 184-189.	0.8	22
146	Electrical and Recombination Properties of Copper-Silicide Precipitates in Silicon. Journal of the Electrochemical Society, 1998, 145, 3889-3898.	1.3	95
147	The Nature of the Electronic States of Cu<sub>3</sub>/sub>Si-Precipitates in Silicon. Solid State Phenomena, 1998, 63-64, 369-374.	0.3	10
148	Epitaxial growth of CuInS <sub>2</sub> on sulphur terminated Si(001). Applied Physics Letters, 1998, 72, 2733-2735.	1.5	42
149	Nonconservative Ostwald ripening of dislocation loops in silicon. Applied Physics Letters, 1998, 73, 2956-2958.	1.5	4
150	Nanoscale Observation of a Grain Boundary Related Growth Mode in Thin Film Reactions. Physical Review Letters, 1998, 80, 774-777.	2.9	31
151	Phosphorous-diffusion gettering in the presence of a nonequilibrium concentration of silicon interstitials: A quantitative model. Physical Review B, 1997, 55, 9577-9583.	1.1	38
152	Kinetics of ion-beam-induced interfacial amorphization in silicon. Journal of Applied Physics, 1997, 82, 5360-5373.	1.1	19
153	Depth Dependence of Dislocation Loop Dissolution Kinetics in Ion Implanted Silicon. Solid State Phenomena, 1997, 57-58, 377-382.	0.3	4
154	Epitaxial heterojunction devices. Solar Energy Materials and Solar Cells, 1997, 49, 337-342.	3.0	5
155	Behaviour of the Size Distribution Function of End-of-Range Dislocation Loops during Silicon Oxidation. Solid State Phenomena, 1996, 47-48, 205-210.	0.3	3
156	Structural and Electrical Properties of NiSi<sub>2</sub> Particles in Silicon. Solid State Phenomena, 1996, 47-48, 359-364.	0.3	11
157	Temperature dependent EBIC and deep level transient spectroscopy investigation of different types of misfit-dislocations at MOVPE grown GaAs/InGaAs/GaAs-single-quantum wells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 77-81.	1.7	15
158	The temperature dependence of the ion beam induced interfacial amorphization in silicon. Applied Physics Letters, 1996, 68, 3425-3427.	1.5	9
159	Quantitative strain mapping using high-resolution electron microscopy. Physica Status Solidi A, 1995, 150, 625-634.	1.7	31
160	An approach to quantitative high-resolution transmission electron microscopy of crystalline materials. Ultramicroscopy, 1995, 58, 131-155.	0.8	139
161	Bandlike and localized states at extended defects in silicon. Physical Review B, 1995, 52, 13726-13729.	1.1	159
162	Mapping projected potential, interfacial roughness, and composition in general crystalline solids by quantitative transmission electron microscopy. Physical Review Letters, 1993, 71, 4150-4153.	2.9	111

#	ARTICLE	IF	CITATIONS
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